

# **LDO Regulator** - High PSRR

#### 150 mA

## **NCP105**

The NCP105 is 150 mA LDO that provides the engineer with a very stable, accurate voltage with low noise suitable for space constrained, noise sensitive applications. In order to optimize performance for battery operated portable applications, the NCP105 employs the dynamic quiescent current adjustment for very low I<sub>O</sub> consumption at no-load.

#### **Features**

- Operating Input Voltage Range: 1.7 V to 5.5 V
- Available in Fixed Voltage Options: 0.8 V to 3.6 V Contact Factory for Other Voltage Options
- Very Low Quiescent Current of Typ. 50 μA
- Soft Start Feature with Two V<sub>OUT</sub> Slew Rate Speed
- Standby Current Consumption: Typ. 0.1 μA
- Low Dropout: 125 mV Typical at 150 mA @ 2.8 V
- ±1% Accuracy at Room Temperature
- High Power Supply Ripple Rejection: 70 dB at 1 kHz
- Thermal Shutdown and Current Limit Protections

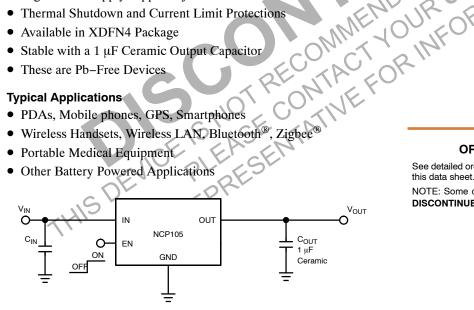


Figure 1. Typical Application Schematic



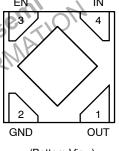
#### **MARKING DIAGRAM**



XX = Specific Device Code = Date Code

\*Date Code orientation and/or position may vary depending upon manufacturing location.

#### PIN CONNECTIONS

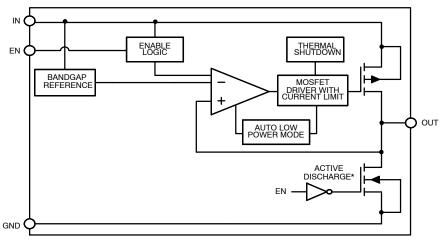


(Bottom View)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 14 of

NOTE: Some of the devices on this data sheet have been DISCONTINUED. Please refer to the table on page 14.



\*Active output discharge function is present only in NCP105A and NCP105C devices. yyy denotes the particular V<sub>OUT</sub> option.

Figure 2. Simplified Schematic Block Diagram

#### PIN FUNCTION DESCRIPTION

PIN FUNC	CTION DESCI	yyy denotes the particular V <sub>OUT</sub> option.  Figure 2. Simplified Schematic Block Diagram
Pin No.	Pin Name	Description
1	OUT	Regulated output voltage pin. A small ceramic capacitor with minimum value of 1 $\mu F$ is needed from this pin to ground to assure stability.
2	GND	Power supply ground.
3	EN	Driving EN over 0.9 V turns on the regulator. Driving EN below 0.4 V puts the regulator into shutdown mode.
4	IN	Input pin. A small capacitor is needed from this pin to ground to assure stability.
-	EPAD	Exposed pad should be connected directly to the GND pin. Soldered to a large ground copper plane allows for effective heat removal.

#### **ABSOLUTE MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Input Voltage (Note 1)	V <sub>IN</sub>	–0.3 V to 6 V	V
Output Voltage	V <sub>OUT</sub>	-0.3 V to V <sub>IN</sub> + 0.3 V or 6 V	V
Enable Input	V <sub>EN</sub>	–0.3 V to 6 V	V
Output Short Circuit Duration	t <sub>SC</sub>	∞	s
Maximum Junction Temperature	$T_{J(MAX)}$	150	°C
Storage Temperature	T <sub>STG</sub>	-55 to 150	°C
ESD Capability, Human Body Model (Note 2)	ESD <sub>HBM</sub>	2000	V
ESD Capability, Machine Model (Note 2)	ESD <sub>MM</sub>	200	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.

- This device series incorporates ESD protection and is tested by the following methods:
- - ESD Human Body Model tested per EIA/JESD22-A114, ESD Machine Model tested per EIA/JESD22-A115,
  - Latchup Current Maximum Rating tested per JEDEC standard: JESD78.

#### THERMAL CHARACTERISTICS (Note 3)

Rating	Symbol	Value	Unit
Thermal Characteristics, Thermal Resistance, Junction-to-Air	$R_{\theta JA}$	208	°C/W

3. Single component mounted on 1 oz, FR 4 PCB with 645 mm<sup>2</sup> Cu area.

**ELECTRICAL CHARACTERISTICS**  $-40^{\circ}C \le T_J \le 85^{\circ}C$ ;  $V_{IN} = V_{OUT(NOM)} + 1$  V for  $V_{OUT}$  options greater than 1.5 V. Otherwise  $V_{IN} = 2.5$  V, whichever is greater;  $I_{OUT} = 1$  mA,  $C_{IN} = C_{OUT} = 1$   $\mu$ F, unless otherwise noted.  $V_{EN} = 0.9$  V. Typical values are at  $T_J = +25^{\circ}C$ . Min./Max. are for  $T_J = -40^{\circ}C$  and  $T_J = +85^{\circ}C$  respectively (Note 4).

Parameter	Test Conditions		Symbol	Min	Тур	Max	Unit
Operating Input Voltage			V <sub>IN</sub>	1.7		5.5	V
Output Voltage Accuracy	$-40^{\circ}C \le T_J \le 85^{\circ}C$	V <sub>OUT</sub> ≤ 2.0 V	V <sub>OUT</sub>	-40		+40	mV
		V <sub>OUT</sub> > 2.0 V		-2		+2	%
Line Regulation	$V_{OUT} + 0.5 V \le V_{IN} \le 5.5 V_{IN}$	/ (V <sub>IN</sub> ≥ 1.7 V)	Reg <sub>LINE</sub>		0.01	0.1	%/V
Load Regulation	I <sub>OUT</sub> = 1 mA to 150 mA		Reg <sub>LOAD</sub>		6	15	mV
Dropout Voltage (Note 5)	I <sub>OUT</sub> = 150 mA	V <sub>OUT</sub> = 1.8 V	$V_{DO}$		220	330	mV
		V <sub>OUT</sub> = 2.8 V			125	210	
		V <sub>OUT</sub> = 3.3 V			105	165	
Output Current Limit	V <sub>OUT</sub> = 90% V <sub>OUT(nom)</sub>		I <sub>CL</sub>	200	600		mA
Quiescent Current	I <sub>OUT</sub> = 0 mA		IQ		50	95	μΑ
Shutdown Current	V <sub>EN</sub> ≤ 0.4 V, V <sub>IN</sub> = 5.5 V		I <sub>DIS</sub>		0.01	19	μΑ
EN Pin Threshold Voltage High Threshold Low Threshold	V <sub>EN</sub> Voltage increasing V <sub>EN</sub> Voltage decreasing		VEN_HI VEN_LO	0.9	OF.	0.4	V
V <sub>OUT</sub> Slew Rate (Note 6)	V <sub>OUT</sub> = 3.3 V, I <sub>OUT</sub> = 10 mA	Normal (version A and B)	V <sub>OUT_</sub> SR	i	190		mV/μs
		Slow (version C and D)	rase		20		
EN Pin Input Current	V <sub>EN</sub> = 5.5 V	NOV	Olen		0.3	1.0	μΑ
Power Supply Rejection Ratio	$V_{IN} = 3.8 \text{ V}, V_{OUT} = 3.5 \text{ V}$ $I_{OUT} = 10 \text{ mA}$	f = 1 kHz	PSRR		70		dB
Output Noise Voltage	f = 10 Hz to 100 kHz		$V_N$		70		$\mu V_{\text{rms}}$
Thermal Shutdown Temperature	Temperature increasing from $T_J = +25^{\circ}C$		T <sub>SD</sub>		160		°C
Thermal Shutdown Hysteresis	Temperature falling from T <sub>SD</sub>		T <sub>SDH</sub>		20		°C
Active Output Discharge Resistance	V <sub>EN</sub> < 0.4 V, Version A and C only		R <sub>DIS</sub>		100		Ω

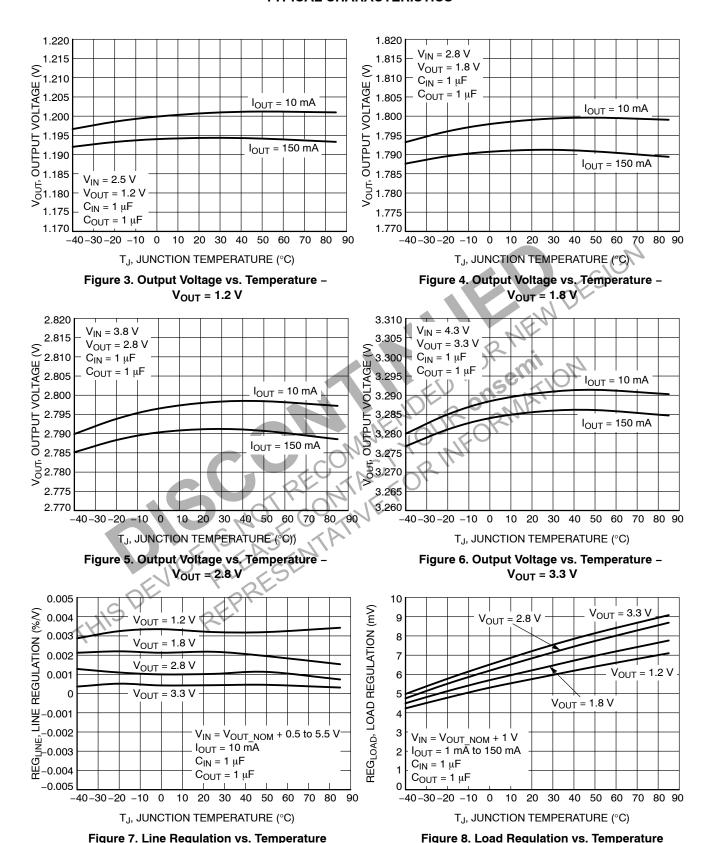
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Performance guaranteed over the indicated operating temperature range by design and/or characterization. Production tested at

T<sub>J</sub> = T<sub>A</sub> = 25°C. Low duty dycle pulse techniques are used during testing to maintain the junction temperature as close to ambient as possible.

5. Characterized when Vour falls 100 mV below the regulated voltage at Vin = VouT(NoM) + 1 V.

6. Please refer OPN to determine slew rate. NCP105A, NCP105B − Normal speed. NCP105C, NCP105D − slower speed.



rigure 6. Load negulation vs. reinperature

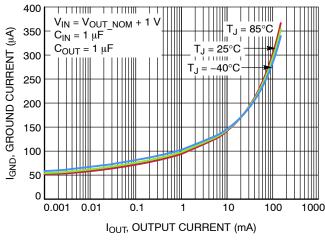


Figure 9. Ground Current vs. Load Current

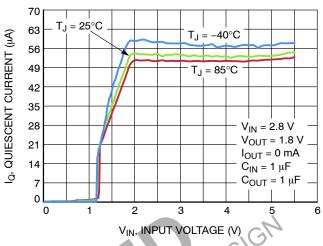


Figure 10. Quiescent Current vs. Input Voltage V<sub>OUT</sub> = 1.8 V

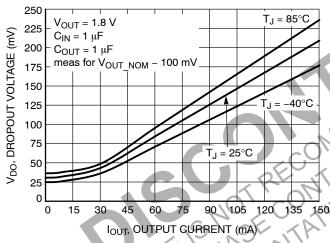


Figure 11. Dropout Voltage vs. Load Current - Vout = 1.8 V

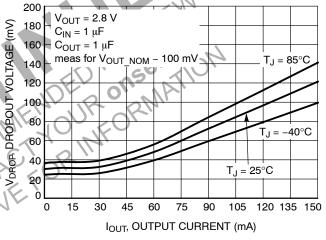


Figure 12. Dropout Voltage vs. Load Current –  $V_{OUT} = 2.8 \text{ V}$ 

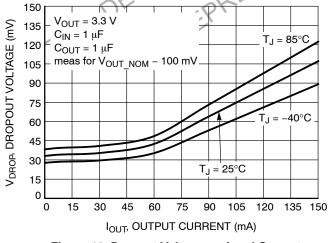


Figure 13. Dropout Voltage vs. Load Current –  $V_{OUT} = 3.3 \text{ V}$ 

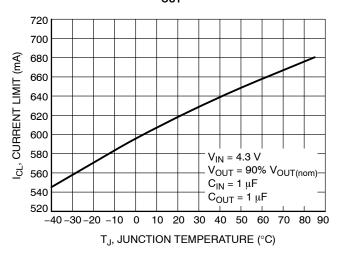
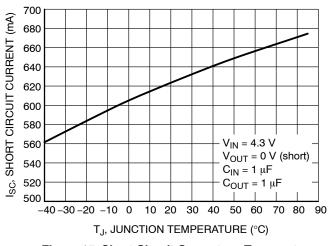


Figure 14. Current Limit vs. Temperature

#### **TYPICAL CHARACTERISTICS**

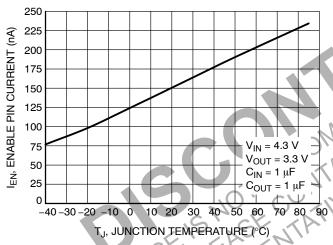
1.0



ENABLE VOLTAGE THRESHOLDS (V) 0.9 OFF -> ON 0.8 0.7 0.6 0.5 ON -> OFF 0.4  $V_{IN} = 3.8 \text{ V}$ 0.3 V<sub>OUT</sub> = 2.8 V 0.2  $C_{IN} = 1 \mu F$ 0.1  $C_{OUT} = 1 \mu F$ Ven, I -40 -30 -20 -10 0 10 20 30 40 50 60 70 80 90 T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

Figure 15. Short Circuit Current vs. Temperature

Figure 16. Enable Thresholds Voltage



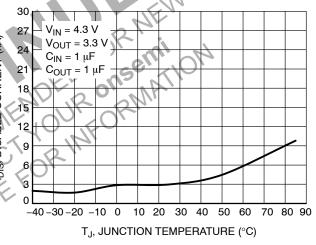
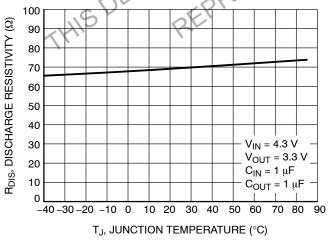


Figure 17. Current to Enable Pin vs. Temperature

Figure 18. Disable Current vs. Temperature



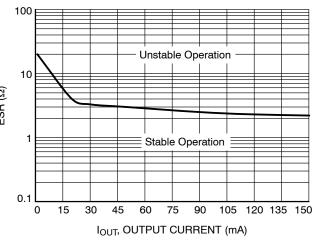
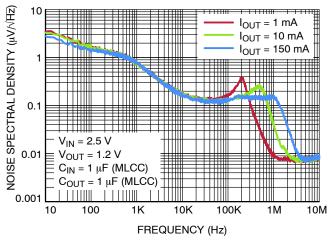
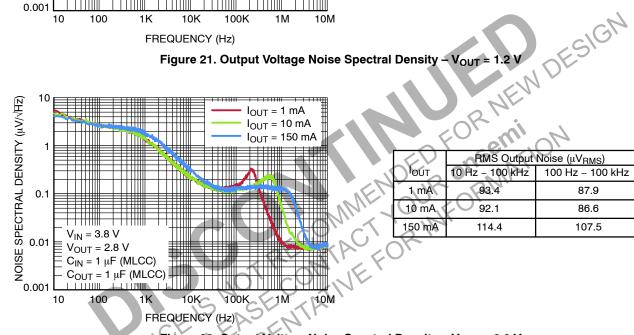


Figure 19. Discharge Resistance vs. Temperature

Figure 20. Maximum C<sub>OUT</sub> ESR Value vs. Load Current

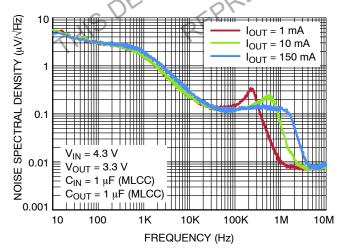


	RMS Output Noise (μV <sub>RMS</sub> )					
I <sub>OUT</sub>	10 Hz – 100 kHz	100 Hz – 100 kHz				
1 mA	65.6	61.9				
10 mA	63.1	59.5				
150 mA	60.8	58.3				



-67	RMS Output Noise (μV <sub>RMS</sub> )				
Тоот	10 Hz – 100 kHz	100 Hz – 100 kHz			
1 mA	93.4	87.9			
10 mA	92.1	86.6			
150 mA	114.4	107.5			

Figure 22. Output Voltage Noise Spectral Density – V<sub>OUT</sub> = 2.8 V



	RMS Output Noise (μV <sub>RMS</sub> )				
lout	10 Hz – 100 kHz   100 Hz – 100 kH				
1 mA	104.0	98.0			
10 mA	102.9	96.7			
150 mA	115.8	110.8			

Figure 23. Output Voltage Noise Spectral Density – V<sub>OUT</sub> = 3.3 V

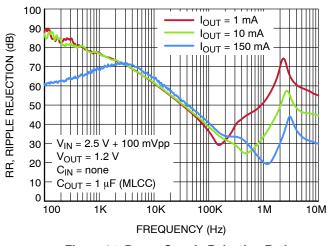


Figure 24. Power Supply Rejection Ratio, V<sub>OUT</sub> = 1.2 V

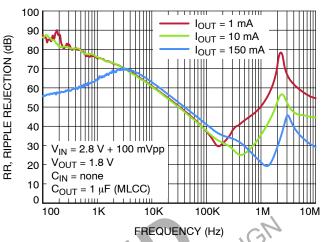


Figure 25. Power Supply Rejection Ratio, V<sub>OUT</sub> = 1.8 V

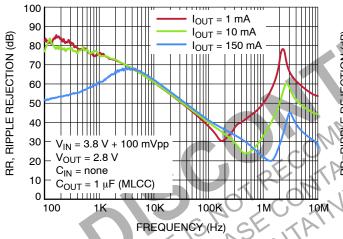


Figure 26. Power Supply Rejection Ratio,

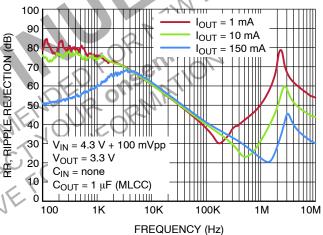
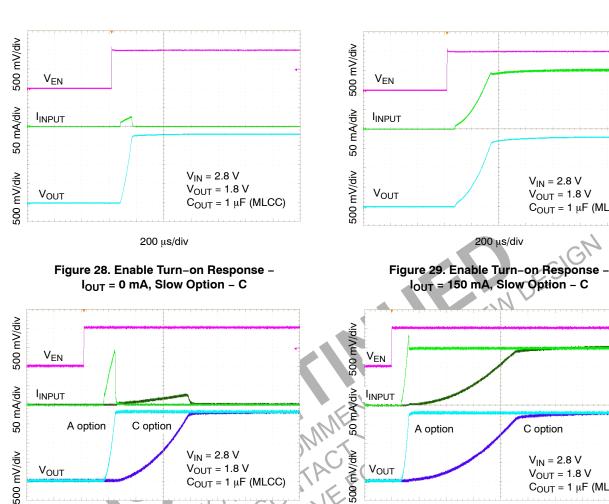


Figure 27. Power Supply Rejection Ratio,  $V_{OUT} = 3.3 \text{ V}$ 

#### **TYPICAL CHARACTERISTICS**



 $V_{OUT} = 1.8 V$ 

 $C_{OUT} = 1 \mu F (MLCC)$ 

Figure 30. V<sub>OUT</sub> Slew-Rate Comparison A and C option - I<sub>OUT</sub> = 10 mA

50 μs/div

 $V_{OUT}$ 

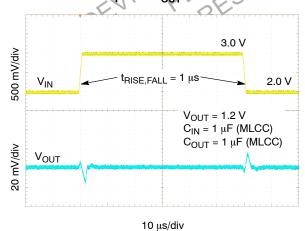
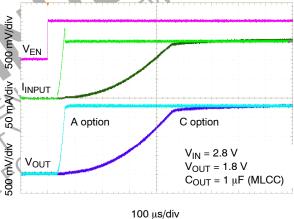


Figure 32. Line Transient Response - $I_{OUT} = 10 \text{ mA}$ 



200 μs/div

 $V_{IN} = 2.8 V$ 

 $V_{OUT} = 1.8 V$ 

 $C_{OUT} = 1 \mu F (MLCC)$ 

Figure 31. V<sub>OUT</sub> Slew-Rate Comparison A and C option –  $I_{OUT}$  = 150 mA

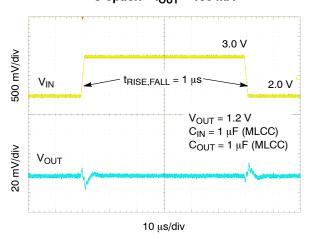
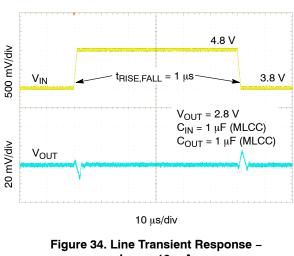


Figure 33. Line Transient Response - $I_{OUT} = 150 \text{ mA}$ 



 $I_{OUT} = 10 \text{ mA}$ 

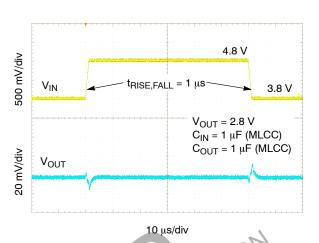
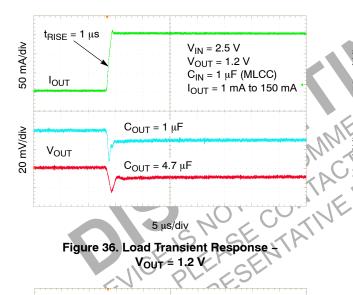


Figure 35. Line Transient Response I<sub>OUT</sub> = 150 mA



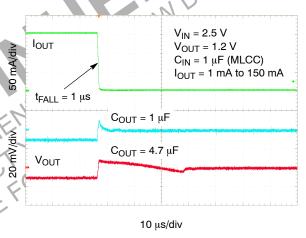


Figure 37. Load Transient Response - $V_{OUT} = 1.2 V$ 

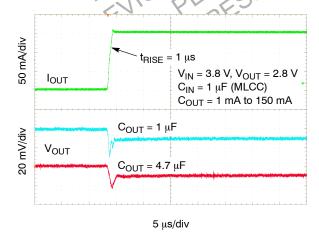


Figure 38. Load Transient Response - $V_{OUT} = 2.8 V$ 

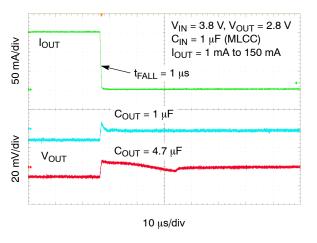


Figure 39. Load Transient Response -**V<sub>OUT</sub>** = 2.8 **V** 

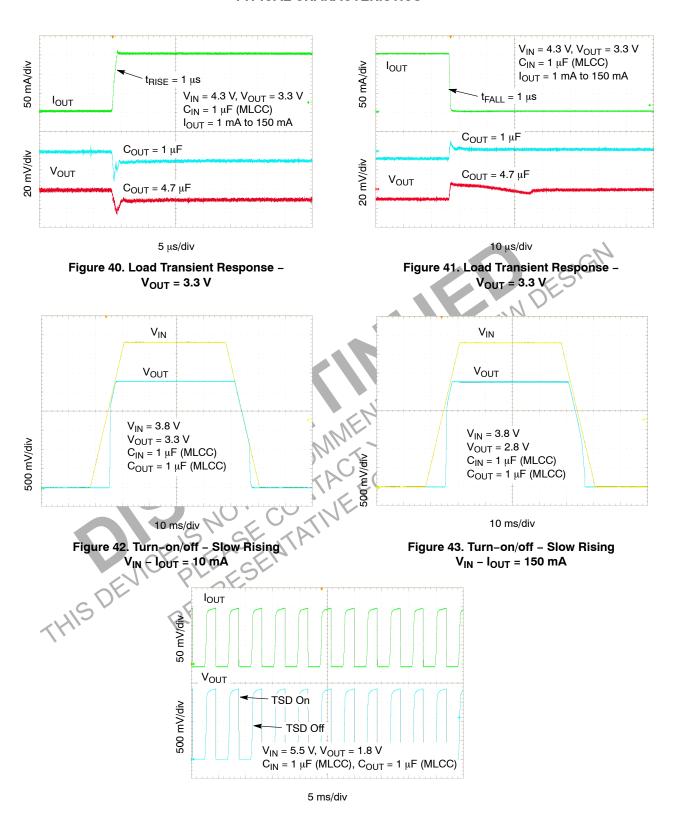


Figure 44. Overheating Protection - TSD

#### APPLICATIONS INFORMATION

#### General

The NCP105 is a high performance 150 mA Low Dropout Linear Regulator. This device delivers very high PSRR (over 70 dB at 1 kHz) and excellent dynamic performance as load/line transients. In connection with very low quiescent current this device is very suitable for various battery powered applications such as tablets, cellular phones, wireless and many others. The device is fully protected in case of output overload, output short circuit condition and overheating, assuring a very robust design.

#### Input Capacitor Selection (CIN)

It is recommended to connect at least a 1  $\mu$ F Ceramic X5R or X7R capacitor as close as possible to the IN pin of the device. This capacitor will provide a low impedance path for unwanted AC signals or noise modulated onto constant input voltage. There is no requirement for the min. /max. ESR of the input capacitor but it is recommended to use ceramic capacitors for their low ESR and ESL. A good input capacitor will limit the influence of input trace inductance and source resistance during sudden load current changes. Larger input capacitor may be necessary if fast and large load transients are encountered in the application.

#### Output Decoupling (COUT)

The NCP105 requires an output capacitor connected as close as possible to the output pin of the regulator. The recommended capacitor value is 1  $\mu F$  and X7R or X5R dielectric due to its low capacitance variations over the specified temperature range. The NCP105 is designed to remain stable with minimum effective capacitance of 0.47  $\mu F$  to account for changes with temperature, DC bias and package size. Especially for small package size capacitors such as 0402 the effective capacitance drops rapidly with the applied DC bias.

There is no requirement for the minimum value of Equivalent Series Resistance (ESR) for the  $C_{\rm OUT}$  but the maximum value of ESR should be less than 1.8  $\Omega$ . Larger output capacitors and lower ESR could improve the load transient response or high frequency PSRR. It is not recommended to use tantalum capacitors on the output due to their large ESR. The equivalent series resistance of tantalum capacitors is also strongly dependent on the temperature, increasing at low temperature.

#### **Enable Operation**

The NCP105 uses the EN pin to enable/disable its device and to deactivate/activate the active discharge function.

If the EN pin voltage is <0.4 V the device is guaranteed to be disabled. The pass transistor is turned–off so that there is virtually no current flow between the IN and OUT. The active discharge transistor is active so that the output voltage  $V_{OUT}$  is pulled to GND through a 100  $\Omega$  resistor. In the

disable state the device consumes as low as typ. 10 nA from the  $V_{\text{IN}}$ .

If the EN pin voltage >0.9 V the device is guaranteed to be enabled. The NCP105 regulates the output voltage and the active discharge transistor is turned–off.

The EN pin has internal pull-down current source with typ. value of 300 nA which assures that the device is turned-off when the EN pin is not connected. In the case where the EN function isn't required the EN should be tied directly to IN.

#### **Output Current Limit**

Output Current is internally limited within the IC to a typical 600 mA. The NCP105 will source this amount of current measured with a voltage drops on the 90% of the nominal  $V_{OUT}$ . If the Output Voltage is directly shorted to ground ( $V_{OUT} = 0$  V), the short circuit protection will limit the output current to 630 mA (typ). The current limit and short circuit protection will work properly over whole temperature range and also input voltage range. There is no limitation for the short circuit duration.

### Thermal Shutdown

When the die temperature exceeds the Thermal Shutdown threshold ( $T_{SD}$  –  $160^{\circ}$ C typical), Thermal Shutdown event is detected and the device is disabled. The IC will remain in this state until the die temperature decreases below the Thermal Shutdown Reset threshold ( $T_{SDU}$  –  $140^{\circ}$ C typical). Once the IC temperature falls below the  $140^{\circ}$ C the LDO is enabled again. The thermal shutdown feature provides the protection from a catastrophic device failure due to accidental overheating. This protection is not intended to be used as a substitute for proper heat sinking.

#### **Power Dissipation**

As power dissipated in the NCP105 increases, it might become necessary to provide some thermal relief. The maximum power dissipation supported by the device is dependent upon board design and layout. Mounting pad configuration on the PCB, the board material, and the ambient temperature affect the rate of junction temperature rise for the part.

The maximum power dissipation the NCP105 can handle is given by:

$$P_{D(MAX)} = \frac{\left[85^{\circ}C - T_{A}\right]}{\theta_{JA}} \tag{eq. 1}$$

The power dissipated by the NCP105 for given application conditions can be calculated from the following equations:

$$P_{D} \approx V_{IN} (I_{GND}@I_{OUT}) + I_{OUT} (V_{IN} - V_{OUT}) \qquad \text{(eq. 2)}$$

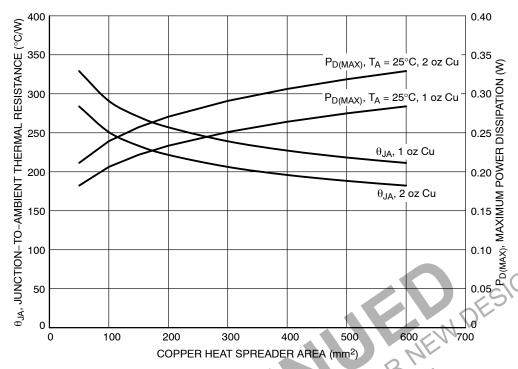


Figure 45.  $\theta_{JA}$  and  $P_{D\ (MAX)}$  vs. Copper Area

#### **Reverse Current**

The PMOS pass transistor has an inherent body diode which will be forward biased in the case that  $V_{OUT} > V_{IN}$ . Due to this fact in cases, where the extended reverse current condition can be anticipated the device may require additional external protection.

#### **Power Supply Rejection Ratio**

The NCP105 features very good Power Supply Rejection ratio. If desired the PSRR at higher frequencies in the range  $100~\rm kHz-10~MHz$  can be tuned by the selection of  $C_{OUT}$  capacitor and proper PCB layout.

#### Turn-On Time

The turn–on time is defined as the time period from EN assertion to the point in which VOUT will reach 98% of its nominal value. This time is dependent on various application conditions such as  $V_{OUT(NOM)}$   $C_{OUT}$  and  $T_A$ .

The NCP105 provides two options of  $V_{OUT}$  ramp-up time. The NCP105A and NCP105B have normal slew rate, typical 190 mV/ $\mu$ s and NCP105C and NCP105D provide slower option with typical value 20 mV/ $\mu$ s which is suitable for camera sensor and other sensitive devices.

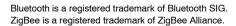
### **PCB Layout Recommendations**

To obtain good transient performance and good regulation characteristics place  $C_{\rm IN}$  and  $C_{\rm OUT}$  capacitors close to the device pins and make the PCB traces wide. In order to minimize the solution size, use 0402 capacitors. Larger copper area connected to the pins will also improve the device thermal resistance. The actual power dissipation can be calculated from the equation above (Equation 2). Expose pad should be tied the shortest path to the GND pin.

#### **ORDERING INFORMATION**

Device	Voltage Option	Marking	Description	Package	Shipping <sup>†</sup>	
NCP105AMX100TCG	1.05 V	TA	150 mA, Active Discharge,	XDFN4	3000 or 5000 /	
NCP105AMX120TCG	1.2 V	TC	Normal Slew-rate	(Pb-Free)	(PD-Free)	Tape & Reel (Note 7)
NCP105AMX180TBG	1.8 V	TD				
NCP105AMX180TCG (Note 7)						
NCP105AMX250TCG	2.5 V	TE				
NCP105AMX280TCG	2.8 V	TF				
NCP105AMX300TCG	3.0 V	TG				
NCP105AMX330TCG	3.3 V	TH				
NCP105AMX345TCG	3.45 V	TJ				

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



<sup>7.</sup> Product processed after October 1, 2022 are shipped with quantity 5000 units / tape & reel.





PIN ONE

REFERENCE

2X \( \sigma 0.05 \( \c)

2X 🔼 0.05 C

// 0.05 C

□ 0.05 C

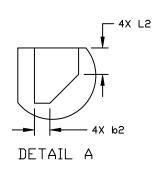
NOTE 4

#### XDFN4 1.0x1.0, 0.65P CASE 711AJ ISSUE C

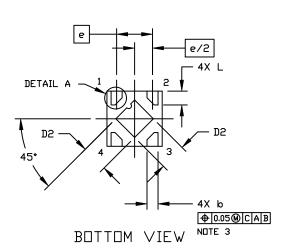
**DATE 08 MAR 2022** 

#### NDTES:

- 1. DIMENSIONING AND TOLERANCING PER. ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSION 6 APPLIES TO THE PLATED TERMINALS AND IS MEASURED BETWEEN 0.15 AND 0.20 FROM THE TERMINAL TIPS.
- 4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.



WEEE 110 111E 1E1111E11						
	MILLIMETERS					
DIM	MIN	NDM	MAX			
Α	0.33	0.38	0.43			
A1	0.00		0.05			
A3	0.10 REF					
b	0.15	0.20	0.25			
b2	0.02	0.07	0.12			
D	0.90	1.00	1.10			
D2	0.43	0.48	0.53			
Ε	0.90	1.00	1.10			
е	0.65 BSC					
L	0.20		0.30			
L2	0.07		0.17			



TOP VIEW

SIDE VIEW

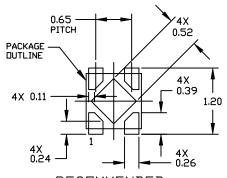
A

В

(A3)

A1

SEATING PLANE



# RECOMMENDED MOUNTING FOOTPRINT

\* FOR ADDITIONAL INFORMATION ON OUR POFFRE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNT TECHNIQUES REFERENCE MANUAL, SOLDERRM/D

# GENERIC MARKING DIAGRAM\*



XX = Specific Device Code M = Date Code \*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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